

2N2222A

NPN Plastic Encapsulated Transistor

RoHS Compliant Product A suffix of "-C" specifies halogen & lead-free

FEATURE

Complementary PNP type available 2N2907A

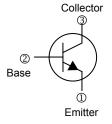
TO-92

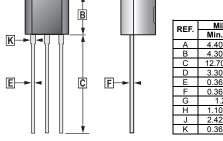




PACKAGING INFORMATION

Weight: 0.2056 g





ABSOLUTE MAXIMUM RATINGS (at T_A = 25°C unless otherwise specified)

| Parameter | Symbol | Ratings | Unit |
|--------------------------------|-----------------------------------|------------------|------------|
| Collector to Base Voltage | V_{CBO} | 75 | V |
| Collector to Emitter Voltage | V_{CEO} | 40 | V |
| Emitter to Base Voltage | V_{EBO} | 6 | V |
| Collector Current – Continuous | Ic | 600 | mA |
| Collector Power Dissipation | Pc | 625 | mW |
| Junction, Storage Temperature | T _J , T _{STG} | +150, -55 ~ +150 | $^{\circ}$ |

ELECTRICAL CHARACTERISTICS (at T_A = 25°C unless otherwise specified)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Test Conditions | |
|---|---------------------------|------|-------|------|------|--|--|
| Collector-Base Breakdown Voltage | $V_{(BR)CBO}$ | 75 | - | - | V | $I_{C} = 10uA, I_{E} = 0$ | |
| Collector-Emitter Breakdown Voltage | V _{(BR)CEO} | 40 | - | - | V | I _C = 10mA, I _B = 0 | |
| Emitter-Base Breakdown Voltage | $V_{(BR)EBO}$ | 6 | - | - | V | $I_E = 10uA, I_C = 0$ | |
| Collector Cut-off Current | I _{CBO} | - | - | 10 | nA | $V_{CB} = 60V, I_{E} = 0$ | |
| Collector Cut-off Current | I _{CEX} | - | - | 10 | nA | V _{CE} = 60V, V _{EB(Off)} = 3V | |
| Emitter Cut-off Current | I _{EBO} | - | - | 100 | nA | V _{EB} = 3V, I _C = 0 | |
| | h _{FE(1)} | 100 | - | 300 | | V _{CE} = 10V, I _C = 150mA | |
| DC Current Gain | h _{FE(2)} | 40 | - | - | | $V_{CE} = 10V, I_{C} = 0.1mA$ | |
| | h _{FE(3)*} | 42 | - | - | | V _{CE} = 10V, I _C = 500mA | |
| Callegates Freittes Catsuration Valtage | V _{CE(sat)(1)} * | - | - 0.6 | 0.6 | V | I _C = 500mA, I _B = 50mA | |
| Collector-Emitter Saturation Voltage | V _{CE(sat)(2)} * | - | - | 0.3 | V | I _C = 150mA, I _B = 15mA | |
| Base-Emitter Saturation Voltage | V _{BE(sat)*} | - | - | 1.2 | V | I _C = 500mA, I _B = 50mA | |
| Delay Time | t _d | - | - | 10 | nS | V_{CC} = 30V, $V_{EB(Off)}$ = -0.5V, I_{C} = 150mA, I_{B1} = 15mA | |
| Rise Time | t _r | - | - | 25 | nS | | |
| Storage Time | ts | - | - | 225 | nS | V _{CC} = 30V, Ic = 150mA, I _{B1} = I _{B2} = 15mA | |
| Fall Time | t _f | - | - | 60 | nS | | |
| Transition Frequency | f⊤ | 300 | - | - | MHz | V _{CE} = 20V, I _C = 20mA, f = 100MHz | |

* Pulse Test

CLASSIFICATION OF h_{FE(1)}

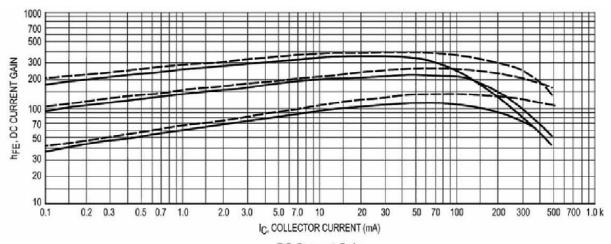
| Rank | L | Н |
|-------|-----------|-----------|
| Range | 100 - 200 | 200 - 300 |

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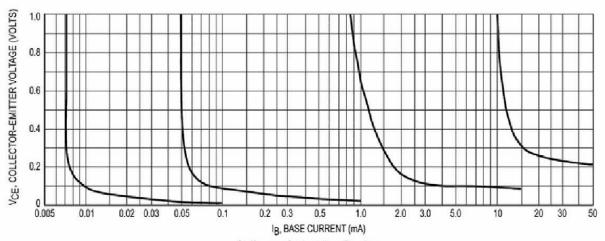


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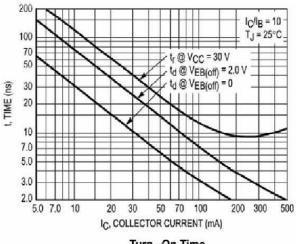
CHARACTERISTIC CURVES



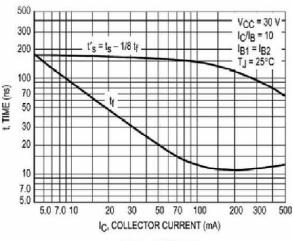
DC Current Gain



Collector Saturation Region



Turn-On Time



Turn-Off Time

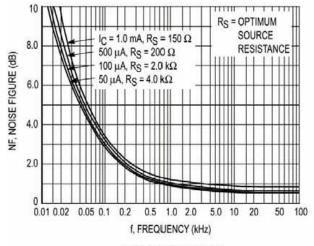
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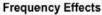


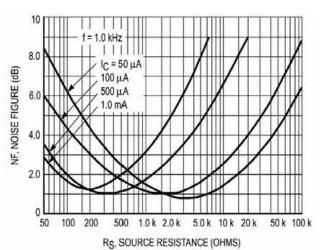
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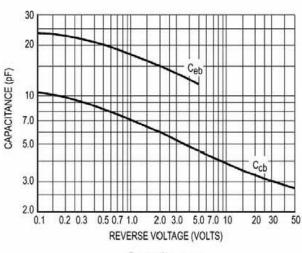
CHARACTERISTIC CURVES



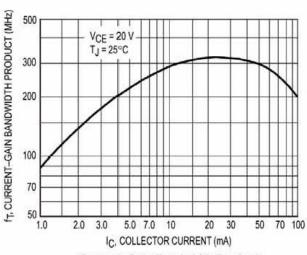




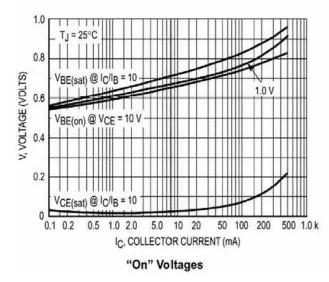
Source Resistance Effects

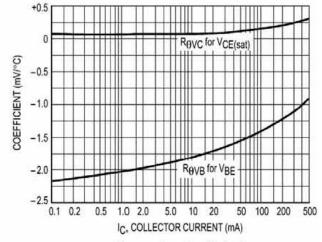


Capacitances



Current-Gain Bandwidth Product





Temperature Coefficients

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